ABSOLUTE MAXIMUM RATINGS

SUPPLY VOLTAGE, $+V_S$ to $-V_S$	350V
OUTPUT CURRENT, continuous	60mA
INPUT VOLTAGE, differential	±16V
INPUT VOLTAGE, common mode	$\pm V_S$
TEMPERATURE, junction	150°C

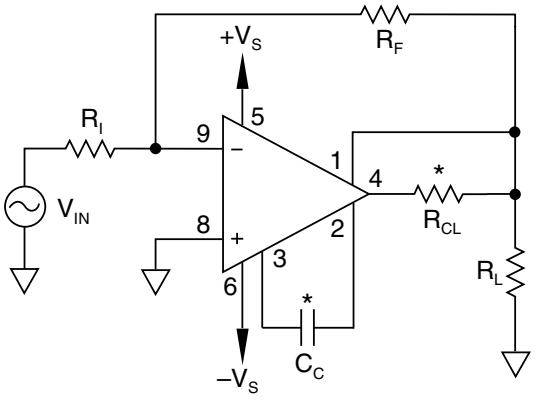
NOTE: Refer to parent product data sheet PA241 for typical AC electrical characteristics, precautions, applications and other test parameters.

DC WAFER PROBED SPECIFICATIONS

PARAMETER	TEST CONDITIONS[1]	MIN	TYP	MAX	UNITS
OFFSET VOLTAGE, initial	V_S = ±50V		15	40	mV
BIAS CURRENT, initial			56	200	pA
COMMON MODE REJECTION	V_{CM} = ±90 V DC	84	94		dB
VOLTAGE SWING	I_O = 40mA	$\pm V_S$–12	$\pm V_S$–10		V
SUPPLY CURRENT, quiescent	V_S = ±50 V	1.8	2.1	2.3	mA

NOTES: 1. Unless otherwise stated V_S = ±50 V, T_A = 25°C, DC input specification ± value given.
2. Sample tested by wafer to 95%.

TYPICAL EXTERNAL CONNECTIONS



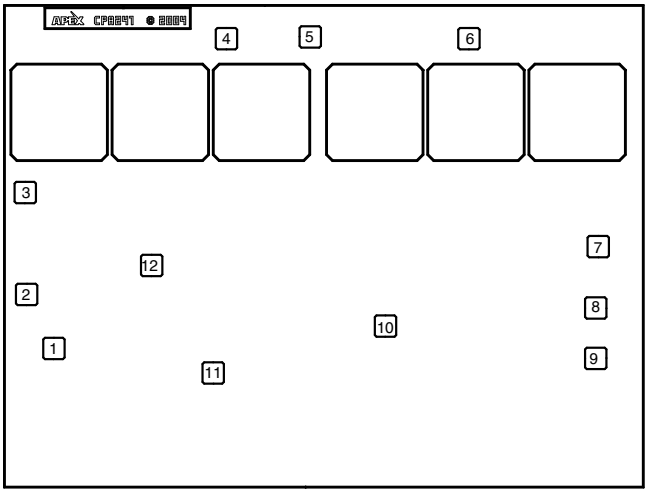
* Required component and value if given.
Optional balance components are recommended values.
C_C is NPO, rated for full supply voltage $-V_S$ to $+V_S$.

NOTE: Diagram for connection illustration only.
All op amp configurations are possible.

Pad	Function	Pad	Function
1	Output	5	+Vs
2	Compensation	6	-Vs
3	Compensation	8	+IN
4	Current Limit	9	-IN

CAUTION The CPA241 is a MOSFET amplifier. ESD handling procedures must be observed

DIE LAYOUT



Dimension: 154.5 x 117.5 ± 2.5 Mils.
Thickness: 15 Mil (380µ).
Backside Metal: None, Silicon.
Bond pad: 5 Mil sq (127µ) Al.
Make no connection to bond pads not listed by function.

Note: The backside of the CPA241 die is isolated up to 500V. The top side walls of the CPA241 die are isolated up to 300V.

Ordering Information:
Order #: CPA241DI80:
Die are only available in waffle packages with a total of 80 die per package.

